

REMARKS

Claims 1-16 are pending in this application. Claims 1-3, 5, 7, 8, 13 and 14 are amended herein.

The amendments to the claims clarify the wording of the claims by reciting that the conductive film is formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate. That the conductive film does not penetrate the insulation film is apparent from the specification, for example, on page 6, lines 2-10, and the drawings.

Claims 1-16 are rejected under 35 U.S.C. 103(a) as unpatentable over Kazue (JP 11-68253) in view of Takemura (JP 4-98841) and further in view of Misawa (U.S. Patent No. 6,150,725).

Applicants respectfully assert that the amendments to the claims further clarify the distinction between the present claims and the cited references. In particular, the Examiner had stated that Kazue discloses an electrode structure where a conductive film (metallic film 13) is formed on a substrate through an insulating film (polyimide layer 12). Applicants note that, in Kazue JP '253, metallic film 13 penetrates polyimide layer 12. The teaching of Kazue is therefore clearly inconsistent with the recitation of the present claims, as amended.

Applicants assert that pending claims 1-16 are novel and non-obvious over Kazue, Takemura and Misawa, taken separately or in combination.

Amendment Accompanying RCE
Shigeo OHSAKA et al.

U.S. Patent Application S.N. 09/456,531
Attorney Docket No. 991387

If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact Applicants undersigned Agent at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

Attached hereto is a marked-up version of the changes made by the current amendment. The attached page is captioned "Version with markings to show changes made."

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully Submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP



Daniel A. Geselowitz, Ph.D.

Agent for Applicants

Reg. No. 42,573

DAG/plb

Atty. Docket No. **991387**
Suite 1000, 1725 K Street, N.W.
Washington, D.C. 20006
(202) 659-2930



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PATENT TRADEMARK OFFICE

Enclosures: Version with markings to show changes made
H:\FLOATERS\DAG\Amendments\991387.amend accompanying rce

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 1-3, 5, 7-8 and 13-14 as follows:

1. (Amended) An electrode structure including a conductive film formed on ~~a base substrate~~
~~through~~ an insulation film without penetrating the insulation film, the insulation film being formed
on a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

2. (Amended) An electrode structure including a conductive film formed on ~~a base substrate~~
~~through~~ an insulation film without penetrating the insulation film, the insulation film being formed
on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

3. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on ~~a base substrate through~~ an insulation film without

penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

5. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on ~~a base substrate through~~ an insulating film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

7. (Twice Amended) A semiconductor light-emitting device according to claim 3, wherein the conductive film is formed on ~~the insulation film through~~ a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

8. (Twice Amended) A semiconductor light-emitting device according to claim 5, wherein the conductive film is formed on ~~the insulation film through~~ a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

13. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a conductive film formed on a ~~base substrate through an~~ insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

14. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a conductive film formed on a ~~base substrate through an~~ insulation film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.